

Abstract Submitted
for the OSF12 Meeting of
The American Physical Society

Ionic-Liquid Gated Bilayer MoS₂ Field-Effect Transistors¹

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¹This work was supported by NSF (No. ECCS-1128297). Part of this research was conducted at the Center for Nanophase Materials Sciences under project # CNMS2011-066.

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Date submitted: 05 Sep 2012

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